



512Kx8 MONOLITHIC SRAM

FEATURES

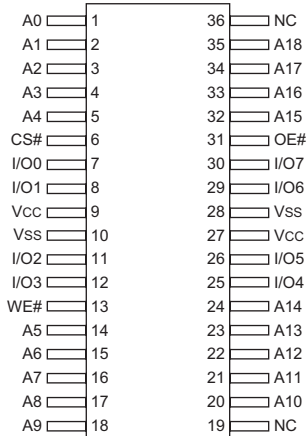
- Access Times 15, 17, 20ns
- Revolutionary, Center Power/Ground Pinout JEDEC Approved
 - 36 lead Ceramic SOJ (Package 100)
 - 36 lead Ceramic Flat Pack (Package 226)
- Evolutionary, Corner Power/Ground Pinout JEDEC Approved
 - 32 pin Ceramic DIP (Package 300)
 - 32 lead Ceramic SOJ (Package 101)
 - 32 lead Ceramic Thinpack™ Flat Pack (Package 321)
- 32 pin, Rectangular Ceramic Leadless Chip Carrier (Package 601)
- Low Power CMOS
- Low Voltage Operation
 - 3.3V ± 10% Power Supply
- Commercial, Industrial and Military Temperature Range
- TTL Compatible Inputs and Outputs
- Fully Static Operation:
 - No clock or refresh required
- Three State Output

* This product is subject to change without notice.

REVOLUTIONARY PINOUT EVOLUTIONARY PINOUT

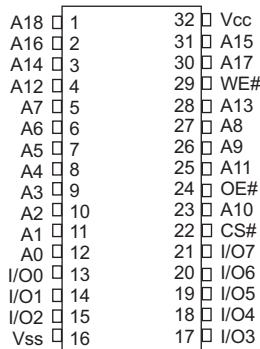
**36 FLAT PACK
36 CSOJ**

TOP VIEW



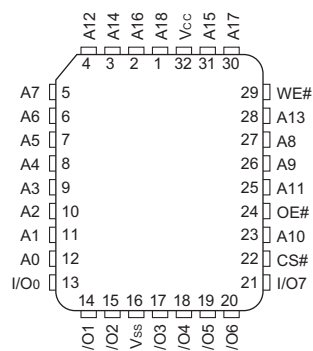
**32 DIP
32 CSOJ (DE)
32 FLAT PACK (FF)**

TOP VIEW



32 CLCC

TOP VIEW



PIN DESCRIPTION

A0-18	Address Inputs
I/O 0-7	Data Input/Output
CS#	Chip Select
OE#	Output Enable
WE#	Write Enable
Vcc	Power Supply
Vss	Ground



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Range to GND	V _G	-0.5	4.6	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	4.6	V

TRUTH TABLE

CS#	OE#	WE#	MODE	DATA I/O	POWER
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active
L	H	H	Out Disable	High Z	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	3.0	3.6	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V
Operating Temp. (Mil)	T _A	-55	+125	°C

CAPACITANCE

T_A = +25°C

Parameter	Symbol	Conditions	Max	Unit
Input capacitance	C _{IN}	V _{IN} = 0 V, f = 1.0 MHz	12	pF
Output capacitance	C _{OUT}	V _{OUT} = 0 V, f = 1.0 MHz	12	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS - CMOS COMPATIBLE

V_{CC} = 5.0V, GND = 0V, -55°C ≤ T_A ≤ 125°C

Parameter	Symbol	Conditions	Min	Max	Unit
Input Leakage Current	I _{LI}	V _{CC} = 3.6, V _{IN} = GND to V _{CC}		10	µA
Output Leakage Current	I _{LO}	CS# = V _{IH} , OE# = V _{IH} , V _{OUT} = GND to V _{CC}		10	µA
Operating Supply Current	I _{CC}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 3.6		100	mA
Standby Current	I _{SS}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 3.6		50	mA
Output Low Voltage	V _{OL}	I _{OL} = 4.0mA		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -4.0mA	2.4		V



AC CHARACTERISTICS

$V_{CC} = 5.0V, GND = 0V, -55^{\circ}C \leq T_A \leq 125^{\circ}C$

Parameter Read Cycle	Symbol	-15		-17		-20		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	t_{RC}	15		17		20		ns
Address Access Time	t_{AA}		15		17		20	ns
Output Hold from Address Change	t_{OH}	0		0		0		ns
Chip Select Access Time	t_{ACS}		15		17		20	ns
Output Enable to Output Valid	t_{OE}		8		8		10	ns
Chip Select to Output in Low Z	t_{CLZ1}	1		1		1		ns
Output Enable to Output in Low Z	t_{OLZ1}	0		0		0		ns
Chip Disable to Output in High Z	t_{CHZ1}		8		8		10	ns
Output Disable to Output in High Z	t_{OHZ1}		8		8		10	ns

1. This parameter is guaranteed by design but not tested.

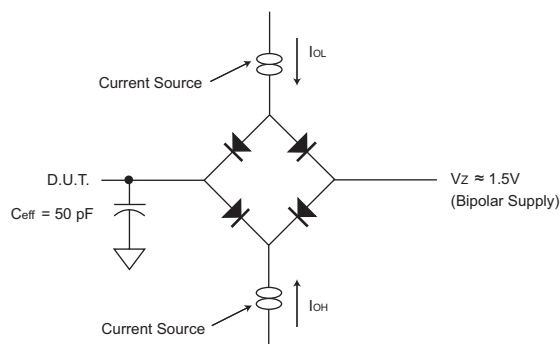
AC CHARACTERISTICS

$V_{CC} = 5.0V, GND = 0V, -55^{\circ}C \leq T_A \leq 125^{\circ}C$

Parameter Write Cycle	Symbol	-15		-17		-20		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	t_{WC}	15		17		20		ns
Chip Select to End of Write	t_{CW}	12		12		14		ns
Address Valid to End of Write	t_{AW}	12		12		14		ns
Data Valid to End of Write	t_{DW}	9		9		10		ns
Write Pulse Width	t_{WP}	12		14		14		ns
Address Setup Time	t_{AS}	0		0		0		ns
Address Hold Time	t_{AH}	0		0		0		ns
Output Active from End of Write	t_{OW1}	2		3		3		ns
Write Enable to Output in High Z	t_{WHZ1}		8		8		9	ns
Data Hold Time	t_{DH}	0		0		0		ns

1. This parameter is guaranteed by design but not tested.

AC TEST CIRCUIT



AC TEST CONDITIONS

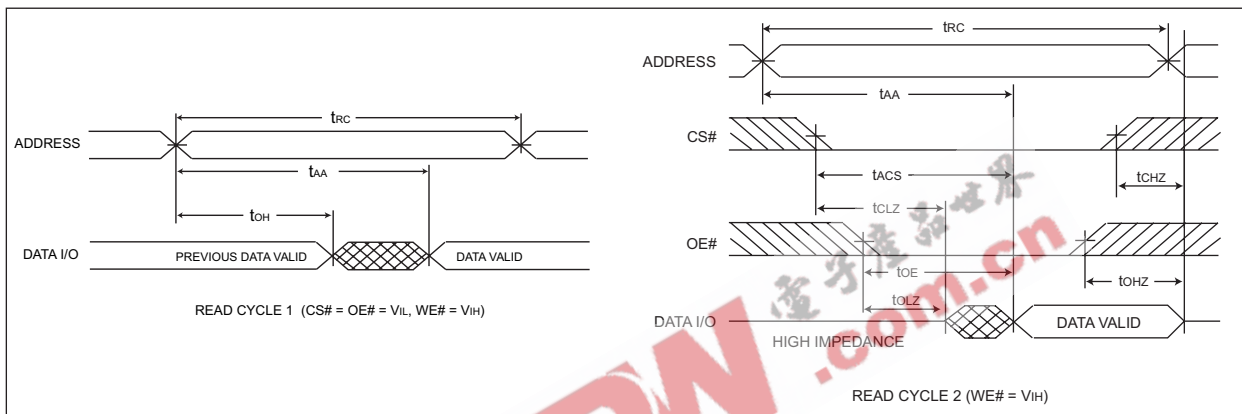
Parameter	Typ	Unit
Input Pulse Levels	$V_{IL} = 0, V_{IH} = 2.5$	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

Notes:

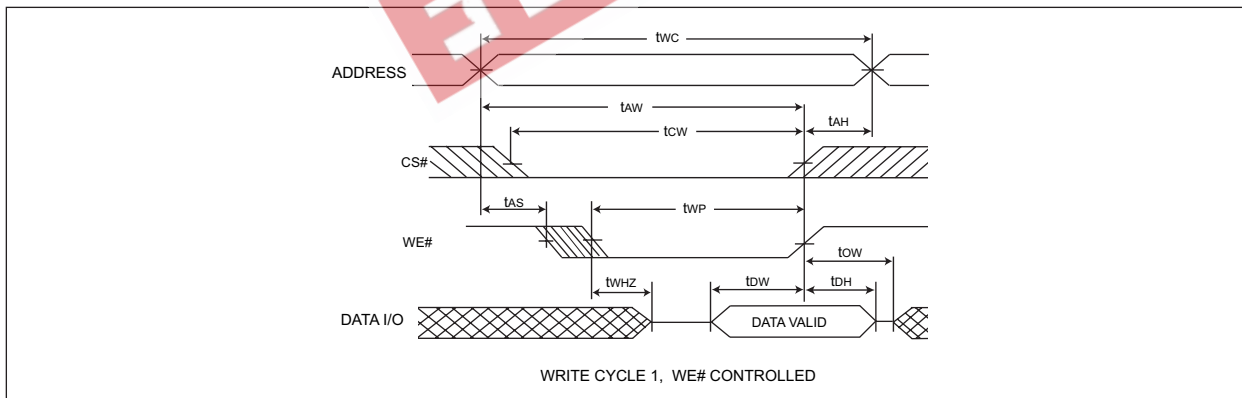
V_Z is programmable from -2V to +7V.
 I_{OL} & I_{OH} programmable from 0 to 16mA.
 Tester Impedance $Z_0 = 75\Omega$.
 V_Z is typically the midpoint of V_{OH} and V_{OL} .
 I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
 ATE tester includes jig capacitance.



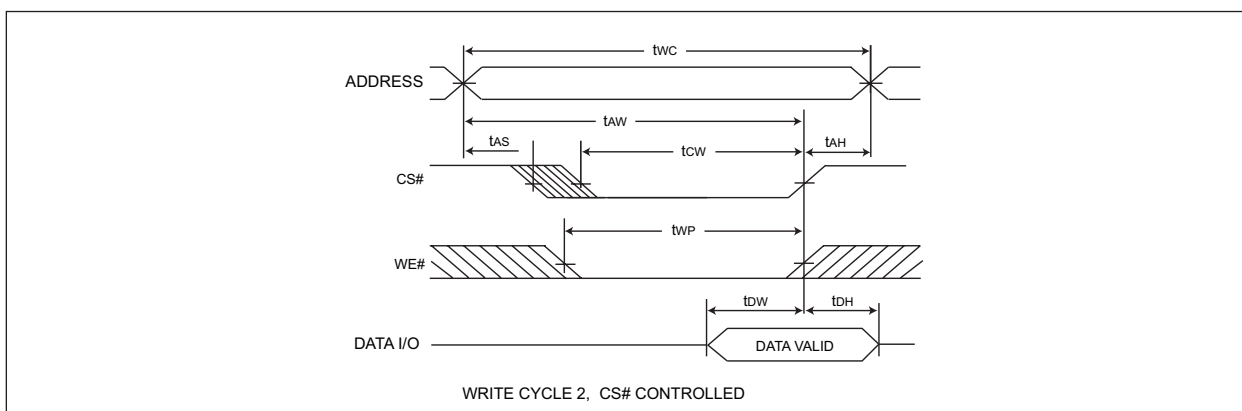
TIMING WAVEFORM - READ CYCLE



WRITE CYCLE - WE# CONTROLLED

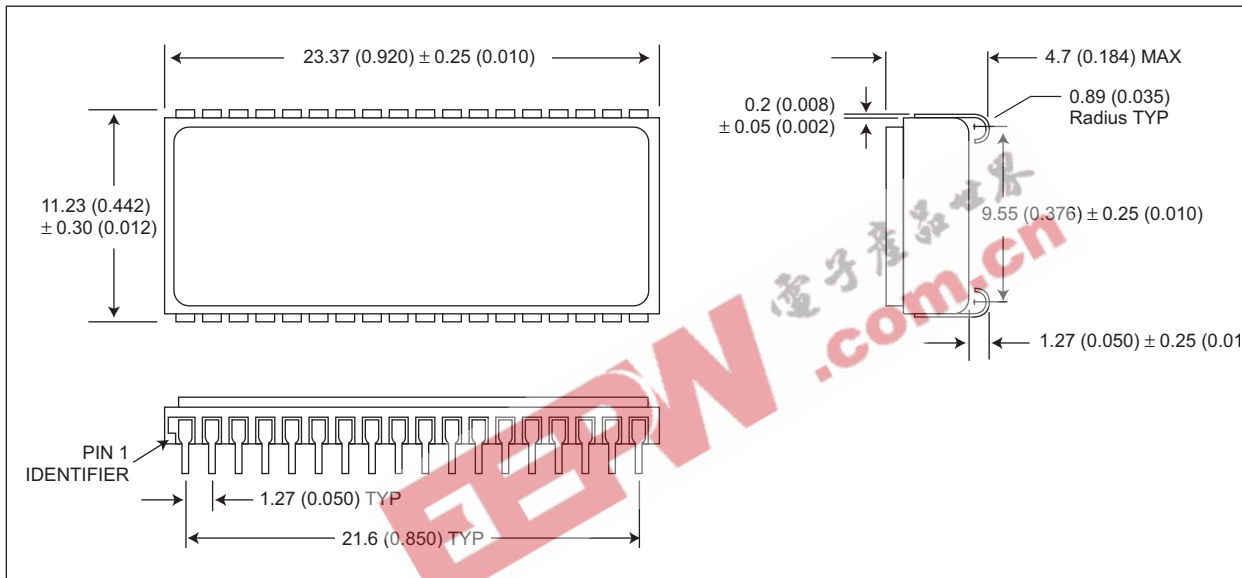


WRITE CYCLE - CS# CONTROLLED



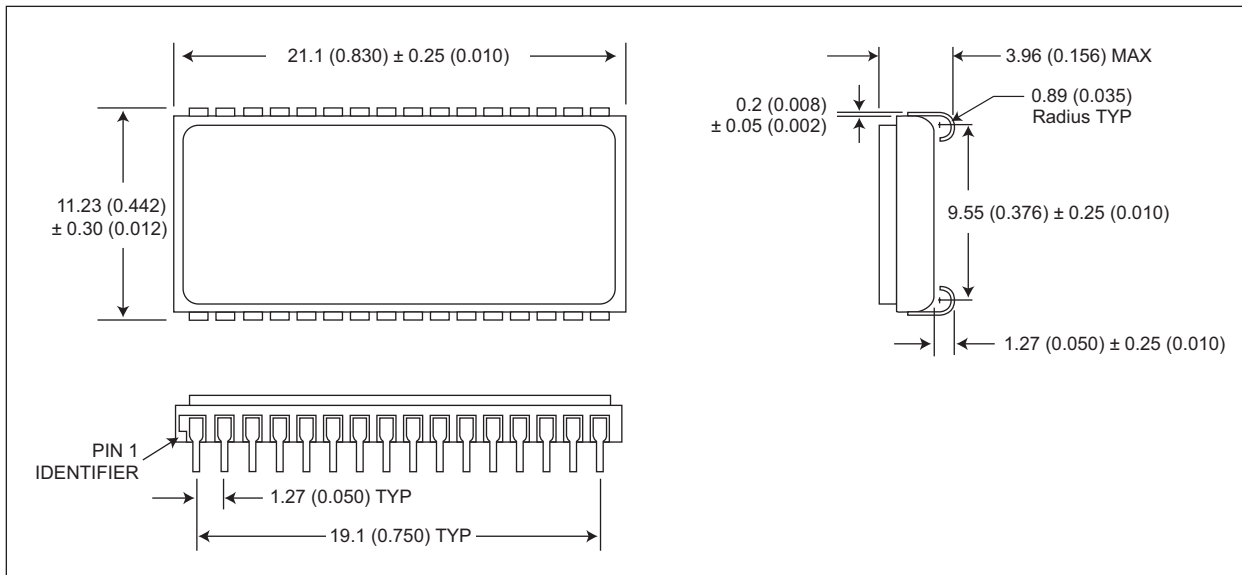


PACKAGE 100: 36 LEAD, CERAMIC SOJ



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

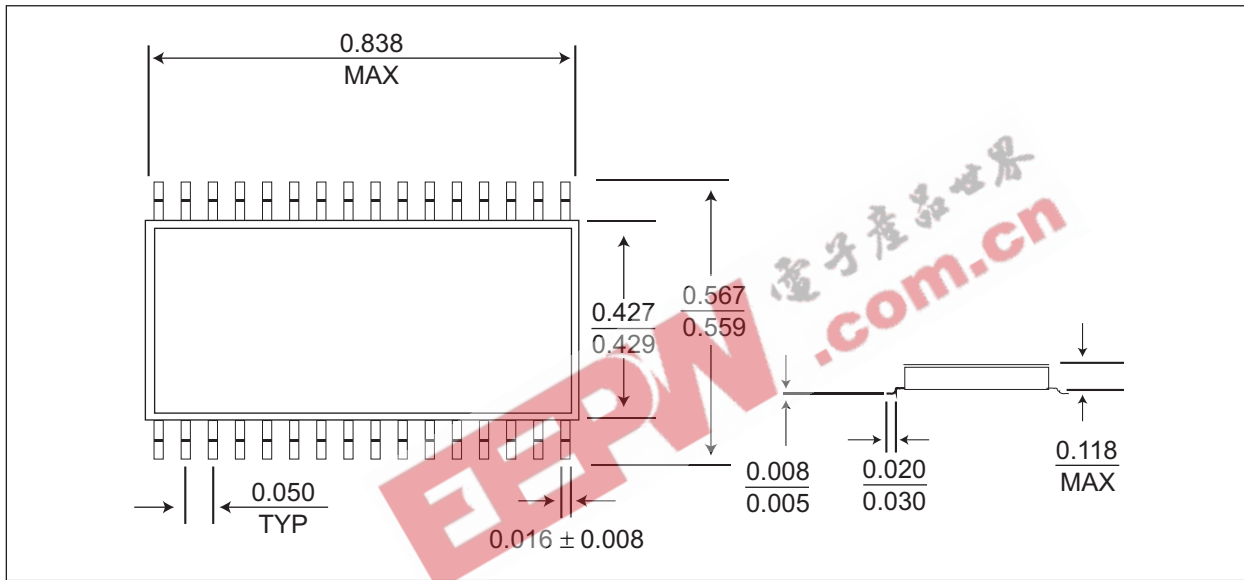
PACKAGE 101: 32 LEAD, CERAMIC SOJ



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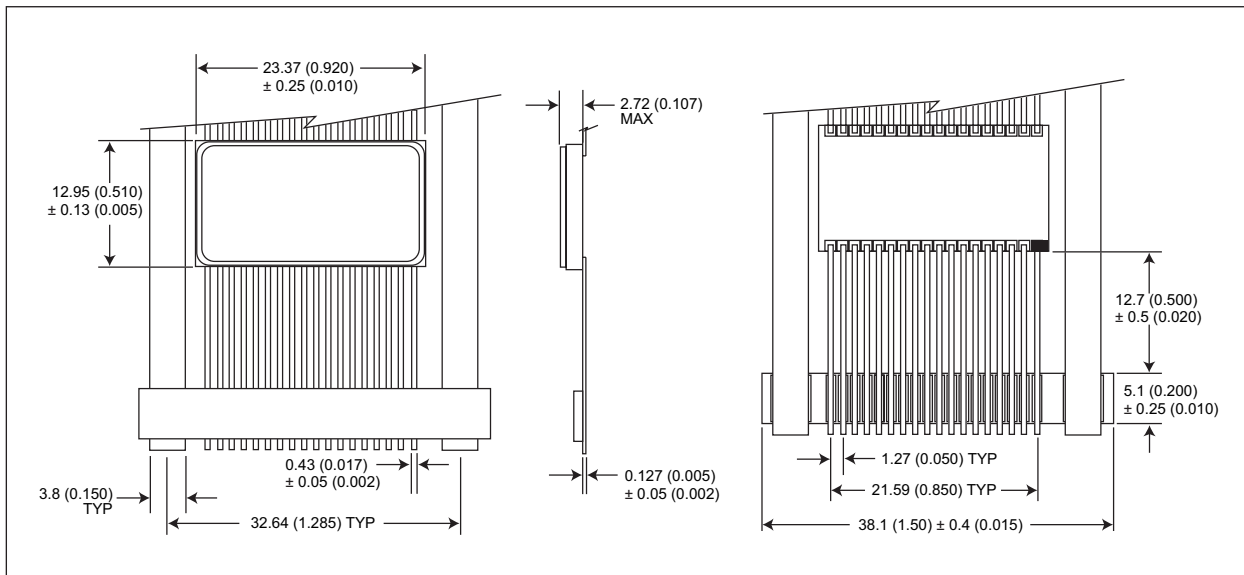


PACKAGE 321: 32 PIN CERAMIC THINPACK™ FLATPACK



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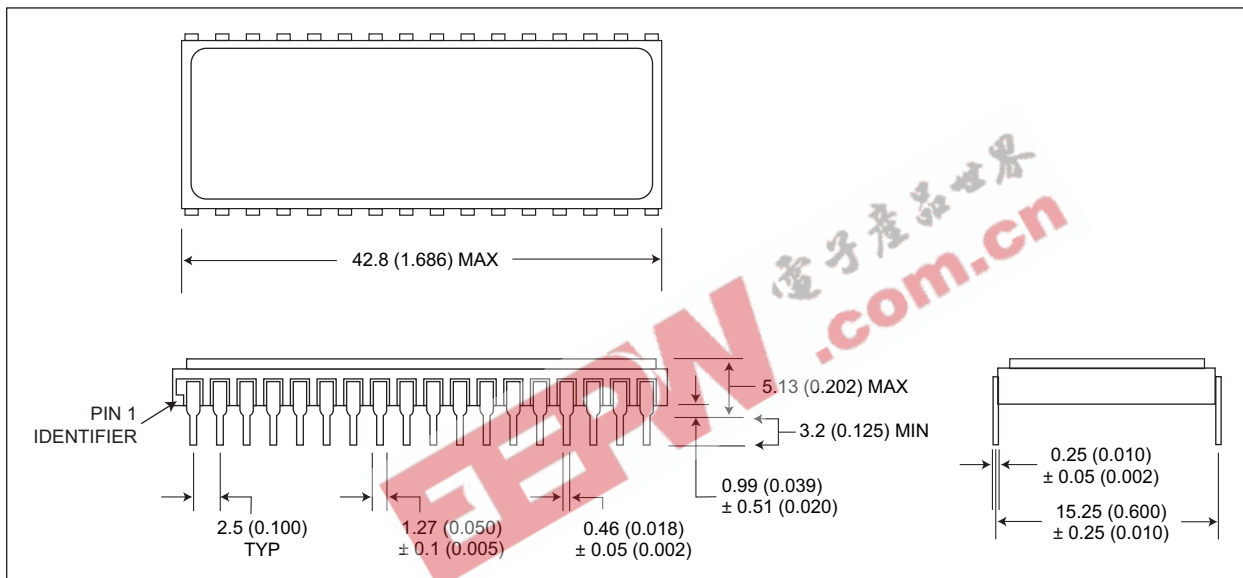
PACKAGE 226: 36 LEAD, CERAMIC FLAT PACK



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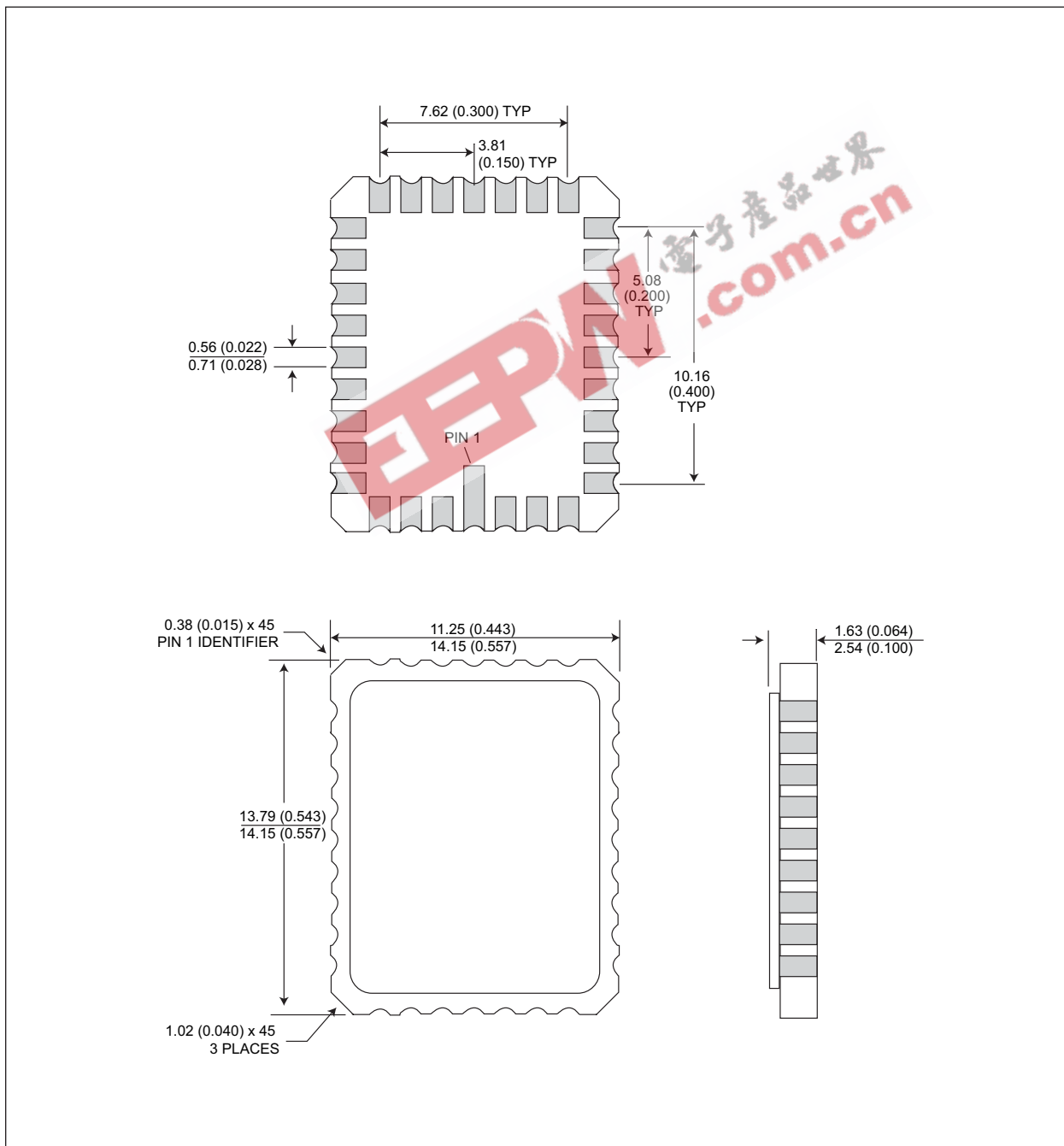
PACKAGE 300: 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



PACKAGE 601: 32 PIN, RECTANGULAR CERAMIC LEADLESS CHIP CARRIER



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



ORDERING INFORMATION

W M S 512K 8 V - XXX X X X

WHITE ELECTRONIC DESIGNS CORP. _____

MONOLITHIC _____

SRAM _____

ORGANIZATION, 512K x 8 _____

LOW VOLTAGE SUPPLY 3.3V ± 10% _____

ACCESS TIME (ns) _____

PACKAGE: _____

C = 32 pin Ceramic 0.600" DIP (Package 300)
 CL = 32 pin Rectangular Ceramic Leadless Chip Carrier (Package 601)
 DE = 32 Lead Ceramic SOJ (Package 101) Evolutionary
 DJ = 36 Lead Ceramic SOJ (Package 100)
 F = 36 Lead Ceramic Flat Pack (Package 226)
 FF = 32 Lead Ceramic Thinpack™ Flat Pack (Package 321)

DEVICE GRADE: _____

M = Military Screened -55°C ≤ T_A ≤ 125°C
 I = Industrial -40°C ≤ T_A ≤ 85°C
 C = Commercial 0°C ≤ T_A ≤ 70°C

LEAD FINISH: _____

Blank = Gold plated leads
 A = Solder dip leads